

Substitute for Form 1449/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete if Known

Application Number	10/607,769
Filing Date	June 27, 2003
First Named Inventor:	Scott A. Hareland
Art Unit	2812
Examiner Name	Such, Matthew W.
Attorney Docket No.:	42P15685

Sheet **1** of **4**

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04/23/2007

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				Examiner Name	Such, Matthew W.
Sheet	3	of	4	Attorney Docket Number	42P15685
NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published			T ²
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